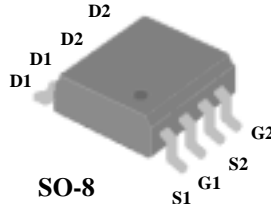




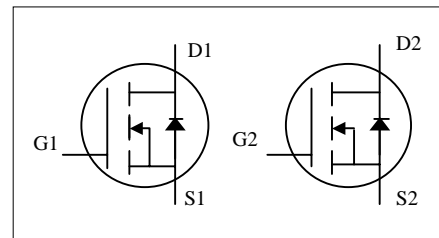
- ▼ Low On-resistance
- ▼ Fast Switching Characteristic
- ▼ Surface Mount Package



CH-1	$BV_{DSS}$	30V
	$R_{DS(ON)}$	18m $\Omega$
	$I_D$	8.5A
CH-2	$BV_{DSS}$	30V
	$R_{DS(ON)}$	26m $\Omega$
	$I_D$	7.3A

## Description

The Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, ruggedized device design, ultra low on-resistance and cost-effectiveness.



## Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		CH-1	CH2	
$V_{DS}$	Drain-Source Voltage	30	30	V
$V_{GS}$	Gate-Source Voltage	$\pm 25$	$\pm 25$	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current <sup>3</sup>	8.5	7.3	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current <sup>3</sup>	6.8	5.8	A
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	30	30	A
$P_D @ T_A = 25^\circ C$	Total Power Dissipation	2.0		W
	Linear Derating Factor	0.016		W/ $^\circ C$
$T_{STG}$	Storage Temperature Range	-55 to 150		$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150		$^\circ C$

## Thermal Data

Symbol	Parameter	Value	Unit
Rthj-a	Thermal Resistance Junction-ambient <sup>3</sup>	Max. 62.5	$^\circ C/W$



# AP6982GM

## CH-1 Electrical Characteristics @ $T_j=25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	-	-	V
$\Delta BV_{DSS}/\Delta T_j$	Breakdown Voltage Temperature Coefficient	Reference to $25^\circ\text{C}, I_D=1\text{mA}$	-	0.03	-	$V/^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=10V, I_D=8A$	-	15	18	$\text{m}\Omega$
		$V_{GS}=4.5V, I_D=6A$	-	23	30	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1	-	3	V
$g_{fs}$	Forward Transconductance	$V_{DS}=10V, I_D=8A$	-	12	-	S
$I_{DSS}$	Drain-Source Leakage Current ( $T_j=25^\circ\text{C}$ )	$V_{DS}=30V, V_{GS}=0V$	-	-	1	$\mu A$
	Drain-Source Leakage Current ( $T_j=70^\circ\text{C}$ )	$V_{DS}=24V, V_{GS}=0V$	-	-	25	$\mu A$
$I_{GSS}$	Gate-Source Leakage	$V_{GS}=\pm 25V$	-	-	$\pm 100$	nA
$Q_g$	Total Gate Charge <sup>2</sup>	$I_D=8A$	-	14	22	nC
$Q_{gs}$	Gate-Source Charge	$V_{DS}=24V$	-	4	-	nC
$Q_{gd}$	Gate-Drain ("Miller") Charge	$V_{GS}=4.5V$	-	8	-	nC
$t_{d(on)}$	Turn-on Delay Time <sup>2</sup>	$V_{DS}=15V$	-	12	-	ns
$t_r$	Rise Time	$I_D=1A$	-	7	-	ns
$t_{d(off)}$	Turn-off Delay Time	$R_G=3.3\Omega, V_{GS}=10V$	-	25	-	ns
$t_f$	Fall Time	$R_D=15\Omega$	-	9	-	ns
$C_{iss}$	Input Capacitance	$V_{GS}=0V$	-	1050	1680	pF
$C_{oss}$	Output Capacitance	$V_{DS}=25V$	-	240	-	pF
$C_{rss}$	Reverse Transfer Capacitance	$f=1.0\text{MHz}$	-	165	-	pF
$R_g$	Gate Resistance	$f=1.0\text{MHz}$	-	1.6	2.4	$\Omega$

## Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{SD}$	Forward On Voltage <sup>2</sup>	$I_S=1.7A, V_{GS}=0V$	-	-	1.2	V
$t_{rr}$	Reverse Recovery Time <sup>2</sup>	$I_S=8A, V_{GS}=0V$	-	23	-	ns
$Q_{rr}$	Reverse Recovery Charge	$dI/dt=100A/\mu s$	-	15	-	nC



**CH-2 Electrical Characteristics @ T<sub>j</sub>=25°C (unless otherwise specified)**

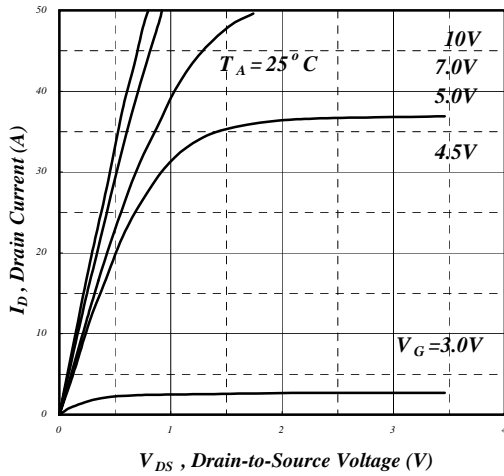
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	30	-	-	V
ΔBV <sub>DSS</sub> /ΔT <sub>j</sub>	Breakdown Voltage Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	-	0.03	-	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =7A	-	22	26	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =5A	-	36	45	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	1	-	3	V
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =10V, I <sub>D</sub> =7A	-	10	-	S
I <sub>DSS</sub>	Drain-Source Leakage Current (T=25°C)	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V	-	-	1	uA
	Drain-Source Leakage Current (T=70°C)	V <sub>DS</sub> =24V, V <sub>GS</sub> =0V	-	-	25	uA
I <sub>GSS</sub>	Gate-Source Leakage	V <sub>GS</sub> =±25V	-	-	±100	nA
Q <sub>g</sub>	Total Gate Charge <sup>2</sup>	I <sub>D</sub> =7A	-	9	15	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =24V	-	3	-	nC
Q <sub>gd</sub>	Gate-Drain ("Miller") Charge	V <sub>GS</sub> =4.5V	-	5	-	nC
t <sub>d(on)</sub>	Turn-on Delay Time <sup>2</sup>	V <sub>DS</sub> =15V	-	9	-	ns
t <sub>r</sub>	Rise Time	I <sub>D</sub> =1A	-	6	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time	R <sub>G</sub> =3.3Ω, V <sub>GS</sub> =10V	-	19	-	ns
t <sub>f</sub>	Fall Time	R <sub>D</sub> =15Ω	-	6	-	ns
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V	-	640	1030	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =25V	-	150	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	f=1.0MHz	-	105	-	pF
R <sub>g</sub>	Gate Resistance	f=1.0MHz	-	1.7	2.5	Ω

**Source-Drain Diode**

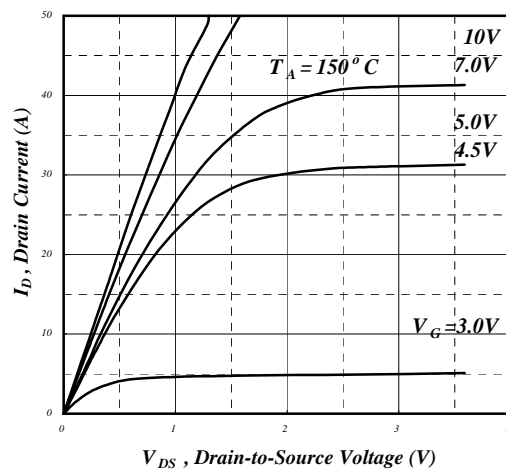
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V <sub>SD</sub>	Forward On Voltage <sup>2</sup>	I <sub>S</sub> =1.7A, V <sub>GS</sub> =0V	-	-	1.2	V
t <sub>rr</sub>	Reverse Recovery Time <sup>2</sup>	I <sub>S</sub> =7A, V <sub>GS</sub> =0V	-	18	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI/dt=100A/μs	-	8	-	nC

**Notes:**

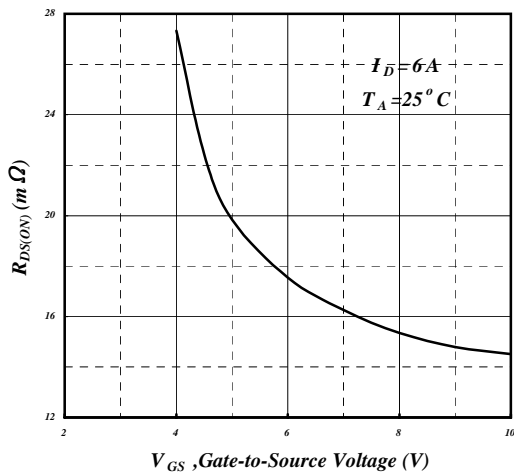
- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse width ≤300us , duty cycle ≤2%.
- 3.Surface mounted on 1 in<sup>2</sup> copper pad of FR4 board , t ≤10sec ; 135°C/W when mounted on min. copper pad.



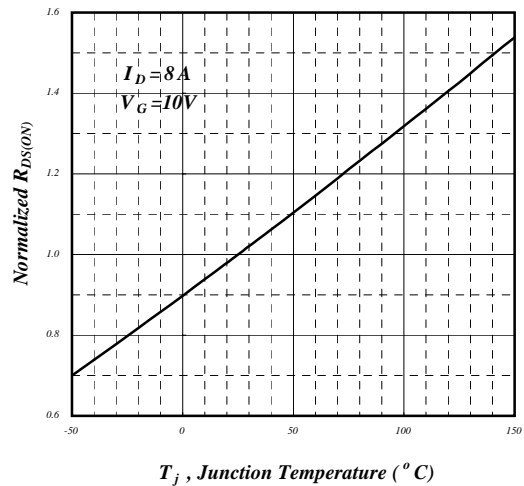
**Fig 1. Typical Output Characteristics**



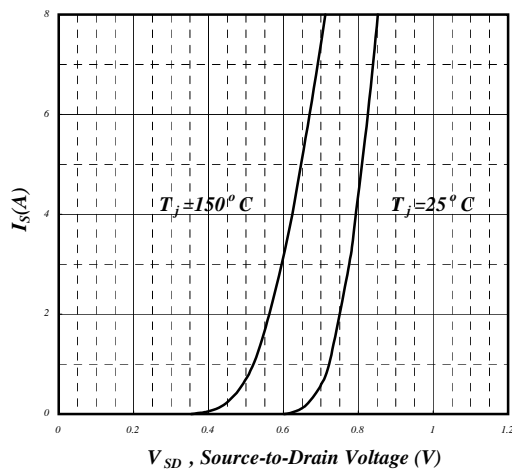
**Fig 2. Typical Output Characteristics**



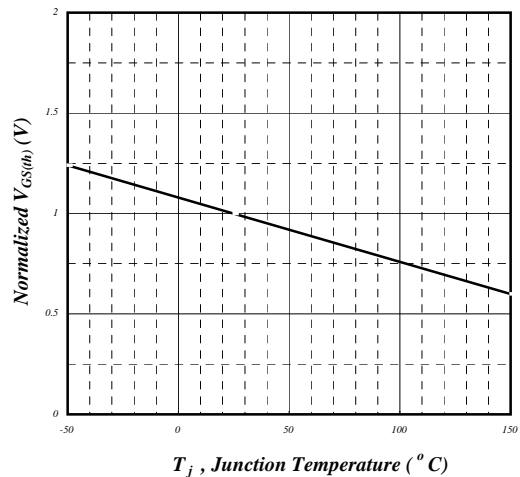
**Fig 3. On-Resistance v.s. Gate Voltage**



**Fig 4. Normalized On-Resistance v.s. Junction Temperature**



**Fig 5. Forward Characteristic of Reverse Diode**



**Fig 6. Gate Threshold Voltage v.s. Junction Temperature**



Channel-1

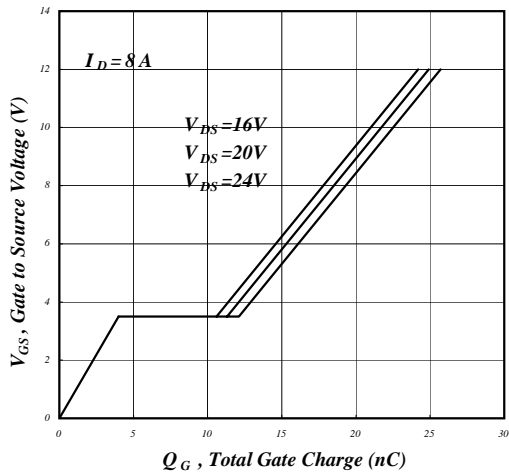


Fig 7. Gate Charge Characteristics

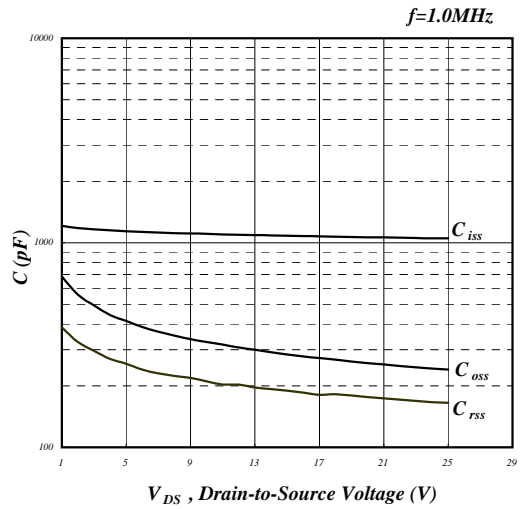


Fig 8. Typical Capacitance Characteristics

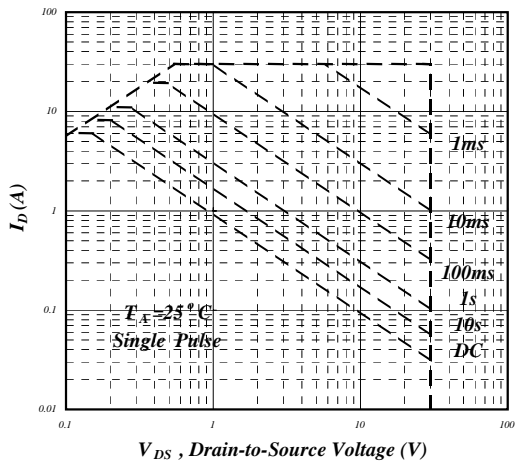


Fig 9. Maximum Safe Operating Area

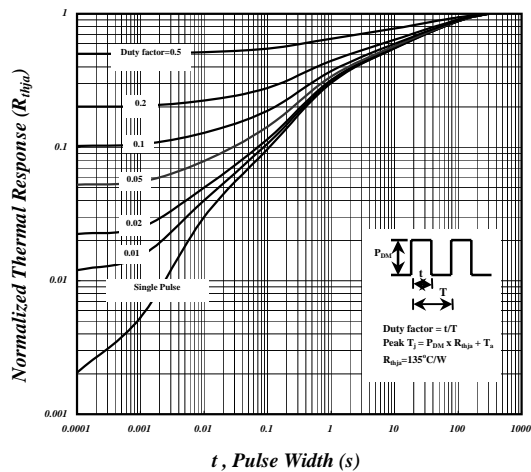


Fig 10. Effective Transient Thermal Impedance

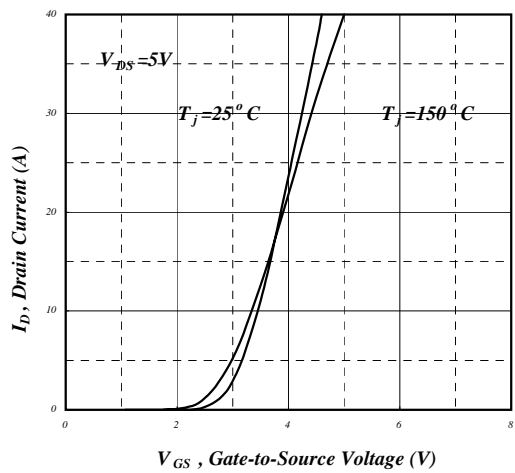


Fig 11. Transfer Characteristics

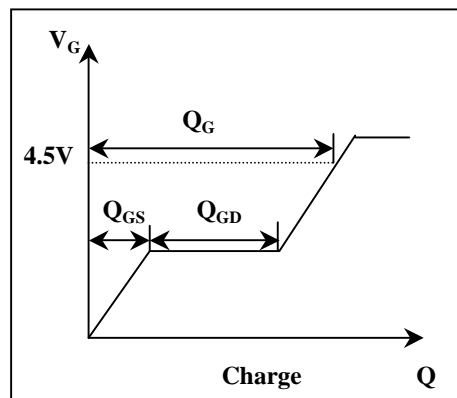
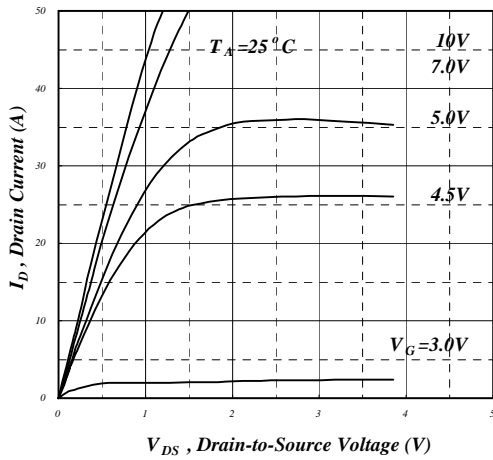


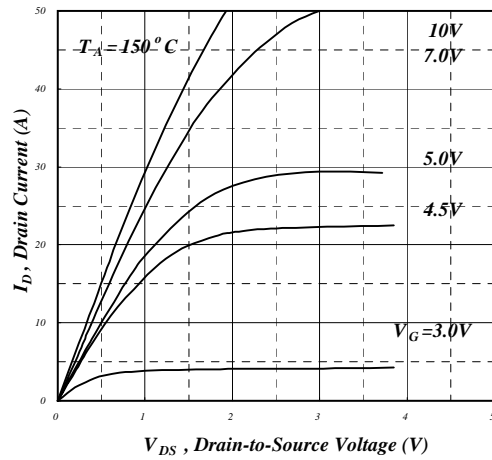
Fig 12. Gate Charge Waveform



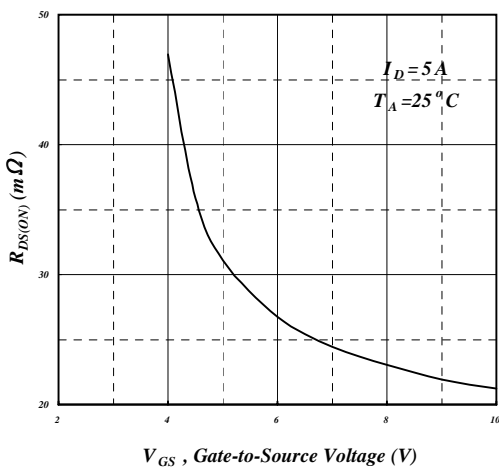
## Channel-2



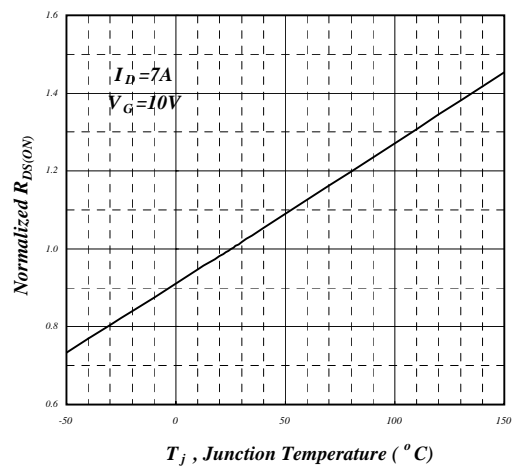
**Fig 1. Typical Output Characteristics**



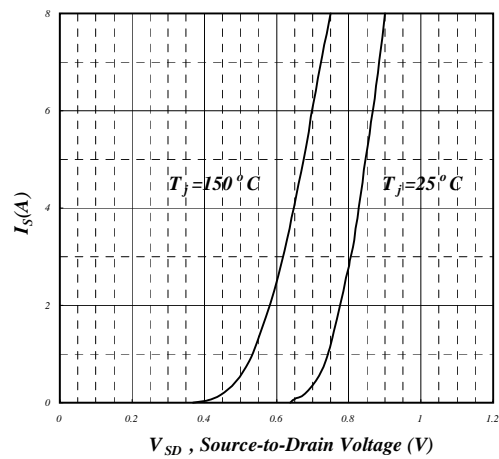
**Fig 2. Typical Output Characteristics**



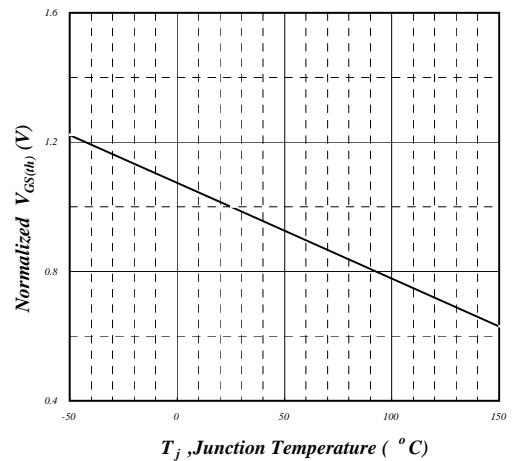
**Fig 3. On-Resistance v.s. Gate Voltage**



**Fig 4. Normalized On-Resistance v.s. Junction Temperature**



**Fig 5. Forward Characteristic of Reverse Diode**



**Fig 6. Gate Threshold Voltage v.s. Junction Temperature**



Channel-2

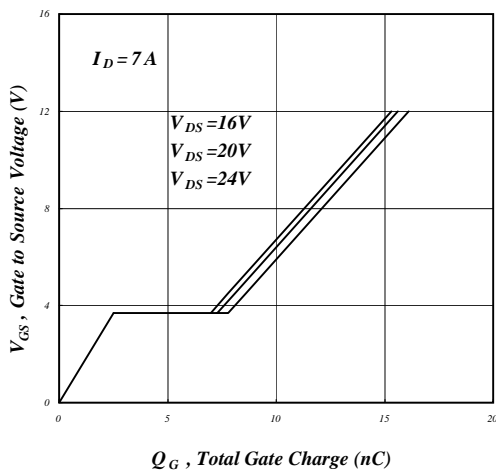


Fig 7. Gate Charge Characteristics

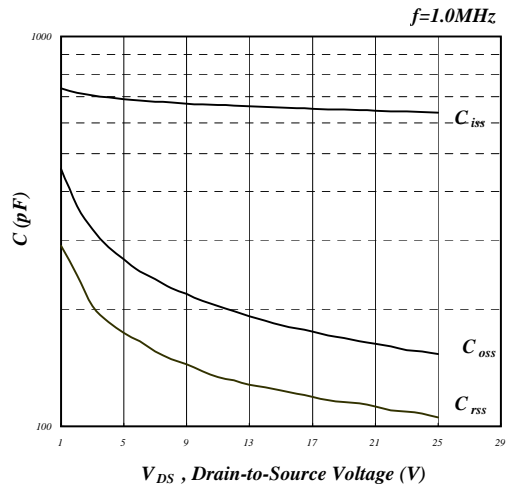


Fig 8. Typical Capacitance Characteristics

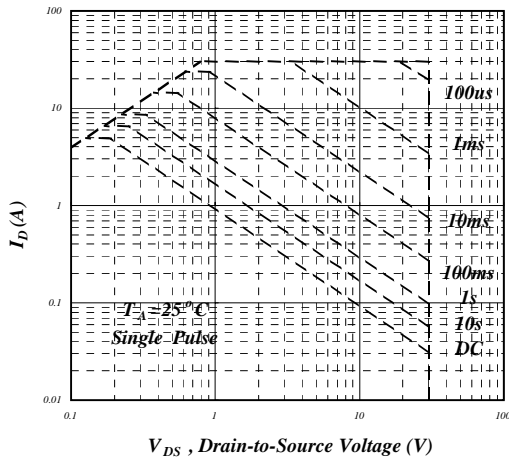


Fig 9. Maximum Safe Operating Area

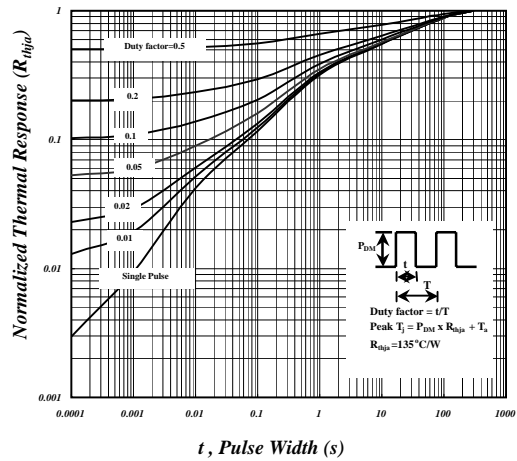


Fig 10. Effective Transient Thermal Impedance

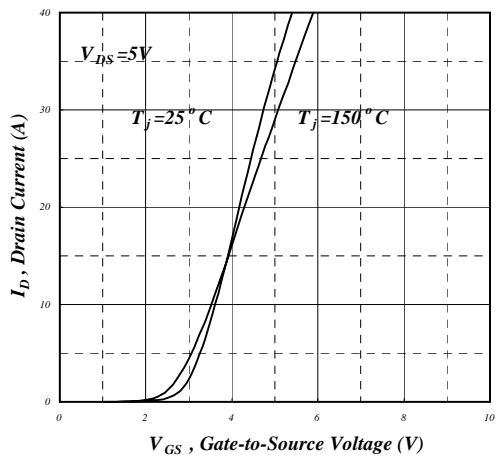


Fig 11. Transfer Characteristics

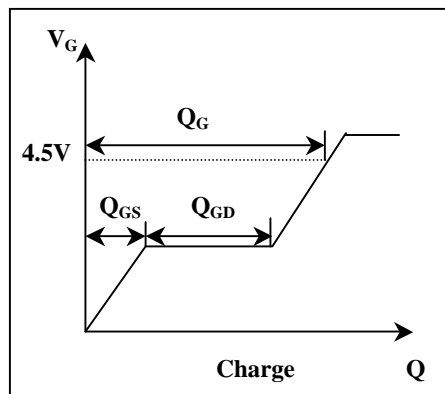


Fig 12. Gate Charge Waveform